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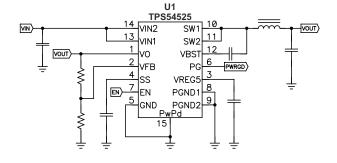
4.5V~18V 入力、5.5A、同期整流式降圧コンバータ

1 特長

- 高速過渡応答を可能にする D-CAP2™ モード
- 低出力リップルで、出力セラミック・コンデンサが使用可
- 広い V_{IN} 入力電圧範囲:4.5V~18V
- 出力電圧範囲:0.76V~5.5V
- 低デューティ・サイクルのアプリケーション に対して最適化された高効率の内蔵 FET $-63m\Omega$ (ハイサイド) および $33m\Omega$ (ローサイド)
- 高効率、シャットダウン時 10µA 未満
- 高い初期バンドギャップ・リファレンス精度
- 調整可能なソフト・スタート
- プリバイアス印加のソフト・スタート
- スイッチング周波数 (f_{SW}):650kHz
- サイクル単位の過電流制限
- パワー・グッド出力

2 アプリケーション

- 幅広い範囲の低電圧システム用アプリケーション
 - デジタル・テレビ用電源
 - 高精細 Blu-ray Disc™ プレーヤ
 - ネットワーク・ホーム・ターミナル
 - デジタル・セットトップ・ボックス (STB)



3 概要

TPS54525 は、適応型オン時間、D-CAP2™ モードの同 期整流式降圧コンバータです。このデバイスを採用するこ とで、各種機器の電源バス・レギュレータに対して、コスト 効果が高く、部品数の少ない、低スタンバイ電流のソリュ ーションを実現できます。本デバイスの主制御ループは、 外部補償部品なしで非常に高速な過渡応答が得られる D-CAP2™ モード制御を使用しています。また、低 ESR (等価直列抵抗)の出力コンデンサ (例: POSCAP、SP-CAP) と超低 ESR セラミック・コンデンサの両方をサポート できる独自の回路も備えています。このデバイスは、4.5V ~18V の VIN 入力で動作します。出力電圧は、0.76V~ 5.5V の範囲でプログラミングできます。また、調整可能な ソフト・スタート時間とパワー・グッド機能も備えています。 TPS54525 は 14 ピンの HTSSOP パッケージで供給さ れ、-40℃~85℃の温度範囲で動作するよう設計されて います。

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製品情報

部品番号	パッケージ	本体サイズ		
TPS54525	HTSSOP	5.00mm × 6.40mm		

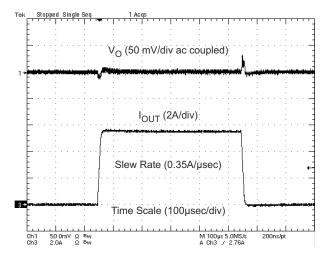




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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

CI	nanges from Revision A (July 2013) to Revision B (April 2021)	Page
•	以下のセクションを追加。「ESD 定格」、「機能説明」、「デバイスの機能モード」、「強制連続導通モード」、「	アプリケー
	ションと実装」、「アプリケーション情報」、「設計要件」、「詳細な設計手順」、「アプリケーション曲線」、「電源に	
	奨事項」、「レイアウト」、「レイアウト例」、「デバイスおよびドキュメントのサポート」、「メカニカル、パッケージ、	および注
	文情報」	
•	文書全体にわたって表、図、相互参照の採番方法を更新	

Updated 式 214



5 Pin Configuration and Functions

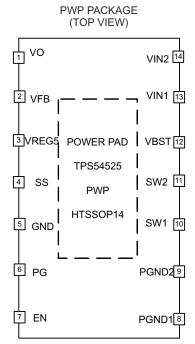


表 5-1. Pin Functions

PIN		DESCRIPTION				
NAME	NO.	DESCRIPTION				
VO	1	Connect to output of converter. This pin is used for output discharge function.				
VFB	2	Converter feedback input. Connect to output voltage with feedback resistor divider.				
VREG5	3	$5.5~V$ power supply output. A capacitor (typical 1 μ F) should be connected to GND. VREG5 is not active when EN is low.				
SS	4	Soft-start control. An external capacitor should be connected to GND.				
GND	5	Signal ground pin				
PG	6	Open drain power good output				
EN	7	Enable control input. EN is active high and must be pulled up to enable the device.				
PGND1, PGND2	8, 9	Ground returns for low-side MOSFET. Also serve as inputs of current comparators. Connect PGND and GND strongly together near the IC.				
SW1, SW2	10, 11	Switch node connection between high-side NFET and low-side NFET. Also serve as inputs to current comparators.				
VBST	12	Supply input for high-side NFET gate driver (boost terminal). Connect capacitor from this pin to respective SW1, SW2 terminals. An internal PN diode is connected between VREG5 to VBST pin.				
VIN1, VIN2	13, 14	Power input and connected to high side NFET drain. Supply input for 5-V internal linear regulator for the control circuitry.				
PowerPAD™	Back side	Thermal pad of the package. Must be soldered to achieve appropriate dissipation. Should be connected to PGND.				



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
	VIN1, VIN2 EN	-0.3	20	V
	VBST	-0.3	26	V
	VBST (10 ns transient)	-0.3	28	V
Input voltage range	VBST (vs SW1, SW2)	-0.3	6.5	V
	VFB, VO, SS, PG	-0.3	6.5	V
	SW1, SW2	-2	20	V
	SW1, SW2 (10 ns transient)	-0.3 20 -0.3 26 -0.3 28 -0.3 6.5 -0.3 6.5	22	V
Output voltage range	VREG5	-0.3	6.5	V
Output voltage range	PGND1, PGND2	-0.3 26 -0.3 28 -0.3 6.5 -0.3 6.5 -2 20 -3 22 -0.3 6.5 -0.3 0.3 -0.2 0.2	V	
Voltage from GND to PowerPa	AD™, V _{diff}	-0.2	0.2	V
Operating junction temperature	re, T _J	-40	150	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VAL	_UE	UNIT
			MIN	ONII	
Storage	temperature, T _{stg}		-55	150	°C
	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	-2000	2000	
V _(ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	-500	500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{IN}	Supply input voltage range		4.5	18	V
		VBST	-0.3	24	
		VBST(10 ns transient)	-0.3	27	
		VBST (vs SW1, SW2)	-0.3	5.7	
		SS, PG	-0.3	5.7	
V_{I}	Input voltage range	EN	-0.3	18	V
		VO, VFB	-0.3	5.5	
		SW1, SW2	-1.8	18	
		SW1, SW2 (10 ns transient)	-3	21	
		PGND1, PGND2	-0.3	0.1	
Vo	Output voltage range	VREG5	-0.3	5.7	V
Io	Output Current range	I _{VREG5}	0	5	mA
T _A	Operating free-air temperature	,	-40	85	°C
T _J	Operating junction temperature		-40	150	°C

6.4 Thermal Information

		TPS54525	
	THERMAL METRIC	PWP	UNITS
		14 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	43.7	
θ_{JCtop}	Junction-to-case (top) thermal resistance	33.1	
θ_{JB}	Junction-to-board thermal resistance	28.4	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.3	
ΨЈВ	Junction-to-board characterization parameter	28.2	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	4.7	

6.5 Electrical Characteristics

over operating free-air temperature range, V_{IN} = 12V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT					
I _{VIN}	Operating - non-switching supply current	V_{IN} current, T_A = 25°C, EN = 5 V, V_{VFB} = 0.8 V		900	1400	μΑ
I _{VINSDN}	Shutdown supply current	V _{IN} current, T _A = 25°C, EN = 0 V		3.6	10	μΑ
LOGIC TI	HRESHOLD				1	
V _{ENH}	EN high-level input voltage		1.6			V
V _{ENL}	EN low-level input voltage				0.6	V
R _{EN}	EN pin resistance to GND	V _{EN} = 12 V	220	440	880	kΩ
VFB VOL	TAGE AND DISCHARGE RESISTANCE				'	
		$T_A = 25$ °C, $V_O = 1.05$ V, continuous mode	757	765	773	
V_{FBTH}	VFB threshold voltage	$T_A = -40$ °C to 85°C, $V_O = 1.05$ V, continuous mode ⁽¹⁾	754		776	mV
I _{VFB}	VFB input current	V _{VFB} = 0.8 V, T _A = 25°C		0	±0.15	μΑ
R _{Dischg}	V _O discharge resistance	V _{EN} = 0 V, V _O = 0.5 V, T _A = 25°C		50	100	Ω
VREG5 O	UTPUT	1				



over operating free-air temperature range, V_{IN} = 12V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{VREG5}	VREG5 output voltage	T _A = 25°C, 6.0 V < V _{IN} < 18 V, 0 < I _{VREG5} < 5 mA	5.2	5.5	5.7	V
V _{VREG5}	VREG5 Line regulation	6.0 V < V _{IN} < 18 V, I _{VREG5} = 5 mA			20	mV
V _{VREG5}	VREG5 Load regulation	0 mA < I _{VREG5} < 5 mA			100	mV
I _{VREG5}	VREG5 Output current	V _{IN} = 6 V, V _{VREG5} = 4 V, T _A = 25°C		60		mA
MOSFET			•			
R _{dsonh}	High side switch resistance	T _A = 25°C, V _{BST} - V _{SW1,2} = 5.5 V		63		mΩ
R _{dsonl}	Low side switch resistance	T _A = 25°C		33		mΩ
CURREN	T LIMIT		1		-	
I _{ocl}	Current limit	L _{OUT} = 1.5 μH ⁽¹⁾	6.1	6.9	8.4	Α
THERMAI	L SHUTDOWN		-			
T	The second of the state of the	Shutdown temperature ⁽¹⁾		165		80
T _{SDN}	Thermal shutdown threshold	Hysteresis ⁽¹⁾		35		°C
ON-TIME	TIMER CONTROL		-			
T _{ON}	On time	V _{IN} = 12 V, V _O = 1.05 V		155		ns
T _{OFF(MIN)}	Minimum off time	T _A = 25°C, V _{VFB} = 0.7 V		260	330	ns
SOFT STA	ART	<u> </u>				
I _{SSC}	SS charge current	V _{SS} = 1 V	4.2	6.0	7.8	μA
I _{SSD}	SS discharge current	V _{SS} = 0.5 V	0.1	0.2		mA
POWER 0	GOOD		1		-	
.,	DO 11 1 1 1	V _{VFB} rising (good)	85	90	95	%
V_{THPG}	PG threshold	V _{VFB} falling (fault)		85		%
I _{PG}	PG sink current	V _{PG} = 0.5 V	2.5	5		mA
OUTPUT	UNDERVOLTAGE AND OVERVOLTA	GE PROTECTION				
V _{OVP}	Output OVP trip threshold	OVP detect	120	125	130	%
T _{OVPDEL}	Output OVP prop delay			10		μs
	Outside III (D trie through ald	UVP detect	60	65	70	%
V_{UVP}	V _{UVP} Output UVP trip threshold Hysteresis			10		%
T _{UVPDEL}	Output UVP delay			0.25		ms
T _{UVPEN}	Output UVP enable delay	Relative to soft-start time		x 1.7		
UVLO		'				
		Wake up VREG5 voltage	3.31	3.61	3.91	
V_{UVLO}	UVLO threshold	Fall VREG5 voltage	2.82	3.12	3.42	V
		Hysteresis VREG5 voltage	0.37	0.49	0.61	

⁽¹⁾ Not production tested.

Product Folder Links: TPS54525

6.6 Typical Characteristics

 V_{IN} = 12 V, T_A = 25 °C (unless otherwise noted)

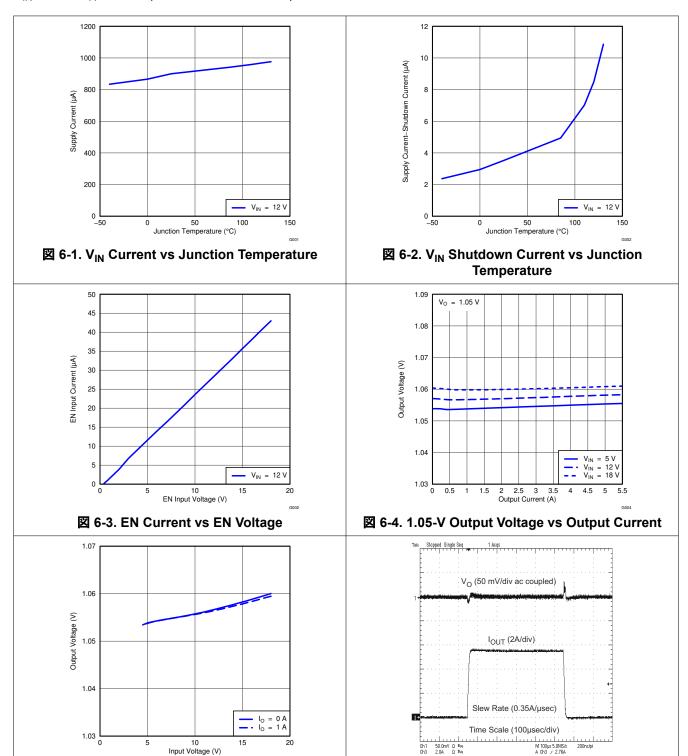
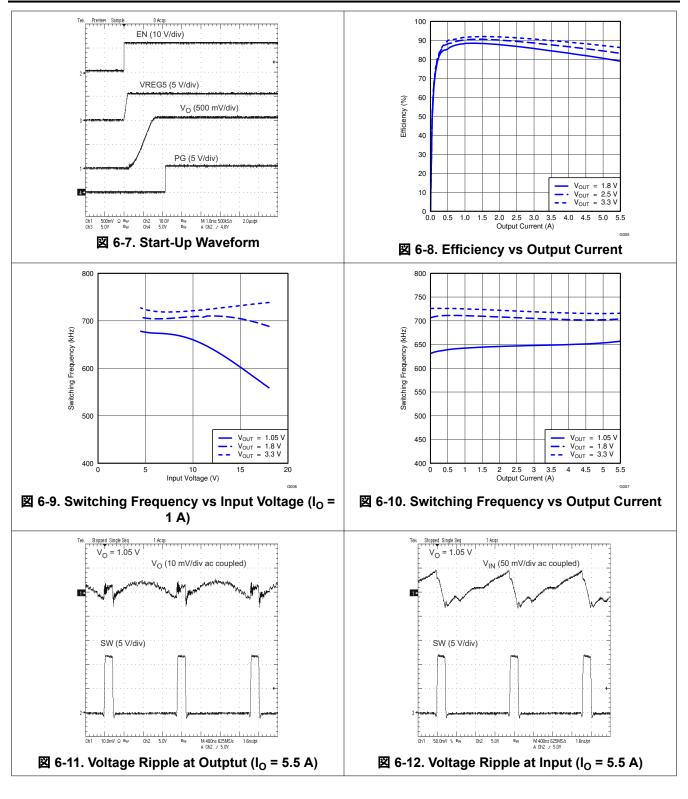


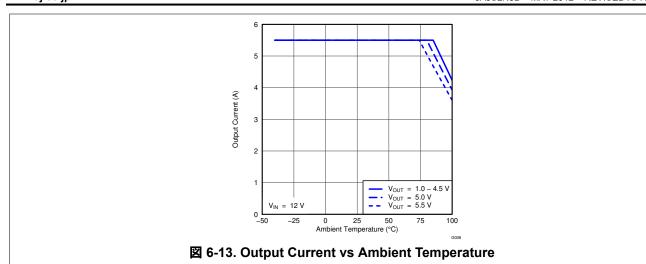
図 6-5. 1.05-V Output Voltage vs Input Voltage

図 6-6. 1.05-V, 50-mA to 5.5-A Load Transient

Response





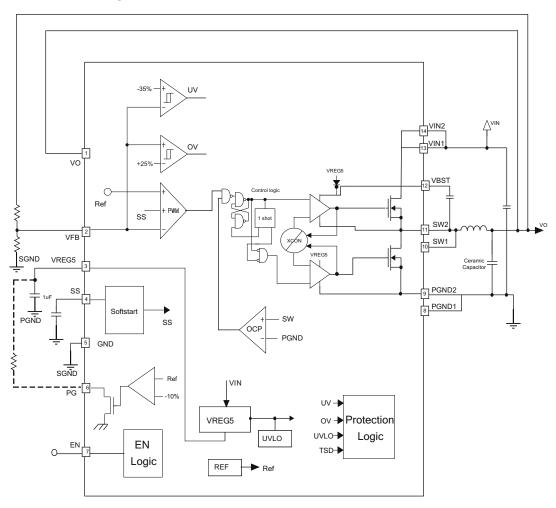


7 Detailed Description

7.1 Overview

The TPS54525 is a 5.5-A synchronous step-down (buck) converter with two integrated N-channel MOSFETs. It operates using D-CAP2™ mode control. The fast transient response of D-CAP2™ control reduces the output capacitance required to meet a specific level of performance. Proprietary internal circuitry allows the use of low ESR output capacitors including ceramic and special polymer types.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 PWM Operation

The main control loop of the TPS54525 is an adaptive on-time pulse width modulation (PWM) controller that supports a proprietary D-CAP2™ mode control. D-CAP2™ mode control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output.

At the beginning of each cycle, the high-side MOSFET is turned on. This MOSFET is turned off after internal one shot timer expires. This one shot is set by the converter input voltage, VIN, and the output voltage, VO, to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The one-shot timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the reference voltage. An internal ramp is added to reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2™ mode control.

7.3.2 PWM Frequency and Adaptive On-Time Control

TPS54525 uses an adaptive on-time control scheme and does not have a dedicated on board oscillator. The TPS54525 runs with a pseudo-constant frequency of 650 kHz by using the input voltage and output voltage to set the on-time one-shot timer. The on-time is inversely proportional to the input voltage and proportional to the output voltage, therefore, when the duty ratio is VOUT/VIN, the frequency is constant.

7.3.3 Soft Start and Pre-Biased Soft Start

The soft start function is adjustable. When the EN pin becomes high, $6-\mu A$ current begins charging the capacitor which is connected from the SS pin to GND. Smooth control of the output voltage is maintained during start up. The equation for the slow start time is shown in \pm 1. VFB voltage is 0.765 V and SS pin source current is 6 μA .

$$t_{SS}(ms) = \frac{C_{SS}(nF) \times V_{REF} \times 1.1}{I_{SS}(\mu A)} = \frac{C_{SS}(nF) \times 0.765 \times 1.1}{6}$$
(1)

The TPS54525 contains a unique circuit to prevent current from being pulled from the output during startup if the output is pre-biased. When the soft-start commands a voltage higher than the pre-bias level (internal soft start becomes greater than feedback voltage V_{FB}), the controller slowly activates synchronous rectification by starting the first low side FET gate driver pulses with a narrow on-time. It then increments that on-time on a cycle-bycycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-bias output, and ensure that the out voltage (VO) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation.

7.3.4 Power Good

The TPS54525 has power-good open drain output. The power good function is activated after soft start has finished. The power good function becomes active after 1.7 times soft-start time. When the output voltage is within -10% of the target value, internal comparators detect power good state and the power good signal becomes high. Rpg resister value ,which is connected between PG and VREG5, is required from $25k\Omega$ to $150k\Omega$. If the feedback voltage goes under 15% of the target value, the power good signal becomes low.

7.3.5 VREG5

VREG5 is an internally generated voltage source used by the TPS54525. It is derived directly from the input voltage and is nominally regulated to 5.5 V when the input voltage is above 5.6 V. The output of the VREG5 regulator is the input to the internal UVLO function. VREG5 must be above the UVLO wake up threshold voltage (3.6 V typical) for the TPS54525 to function. Connect a 1 μ F capacitor between pin 3 of the TPS54525 and power ground for proper regulation of the VREG5 output. The VREG5 output voltage is available for external use. It is recommended to use no more than 5 mA for external loads. The VREG5 output is disabled when the TPS54525 EN pin is open or pulled low.

7.3.6 Output Discharge Control

TPS54525 discharges the output when EN is low, or the controller is turned off by the protection functions (OVP, UVP, UVLO and thermal shutdown). The output is discharged by an internal $50-\Omega$ MOSFET which is connected from VO to PGND. The internal low-side MOSFET is not turned on during the output discharge operation to avoid the possibility of causing negative voltage at the output.

7.3.7 Current Protection

The output overcurrent protection (OCP) is implemented using a cycle-by-cycle valley detect control circuit. The switch current is monitored by measuring the low-side FET switch voltage between the SW pin and GND. This voltage is proportional to the switch current. To improve accuracy, the voltage sensing is temperature compensated.

During the on time of the high-side FET switch, the switch current increases at a linear rate determined by V_{IN} , V_{OUT} , the on-time and the output inductor value. During the on time of the low-side FET switch, this current decreases linearly. The average value of the switch current is the load current I_{OUT} . If the measured voltage is

above the voltage proportional to the current limit, Then, the device constantly monitors the low-side FET switch voltage, which is proportional to the switch current, during the low-side on-time.

The converter maintains the low-side switch on until the measured voltage is below the voltage corresponding to the current limit at which time the switching cycle is terminated and a new switching cycle begins. In subsequent switching cycles, the on-time is set to a fixed value and the current is monitored in the same manner.

There are some important considerations for this type of overcurrent protection. The load current one half of the peak-to-peak inductor current higher than the overcurrent threshold. Also when the current is being limited, the output voltage tends to fall as the demanded load current may be higher than the current available from the converter. This may cause the output undervoltage protection circuit to be activated. When the over current condition is removed, the output voltage returns to the regulated value. This protection is non-latching.

7.3.8 Over/Under Voltage Protection

TPS54525 monitors a resistor divided feedback voltage to detect over and under voltage. When the feedback voltage becomes higher than 125% of the target voltage, the OVP comparator output goes high and the circuit latches as both the high-side and low-side MOSFET drivers turn off. When the feedback voltage becomes lower than 65% of the target voltage, the UVP comparator output goes high and an internal UVP delay counter begins. After 250 μ s, the device latches off both internal top and bottom MOSFET. This function is enabled approximately 1.7 x softstart time.

7.3.9 UVLO Protection

Undervoltage lock out protection (UVLO) monitors the voltage of the V_{REG5} pin. When the V_{REG5} voltage is lower than UVLO threshold voltage, the TPS54525 is shut off. This is protection is non-latching.

7.3.10 Thermal Shutdown

TPS54525 monitors the temperature of itself. If the temperature exceeds the threshold value (typically 165°C), the device is shut off. This is non-latch protection.

7.4 Device Functional Modes

7.4.1 Forced CCM Mode

The TPS54525 operates in Forced CCM (FCCM) mode, which keeps the converter operating in continuous current mode during light-load conditions and allows the inductor current to become negative. During FCCM mode, the switching frequency (FSW) is maintained at an almost constant level over the entire load range, which is suitable for applications requiring tight control of the switching frequency and output voltage ripple at the cost of lower efficiency under light load."

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8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

⊠ 8-1 shows a typical application for TPS54525 with 1.05-V output. This design converts an input voltage range of 4.5 V to 18 V down to 1.05 V with a maximum output current of 5.5 A.

8.2 Typical Application

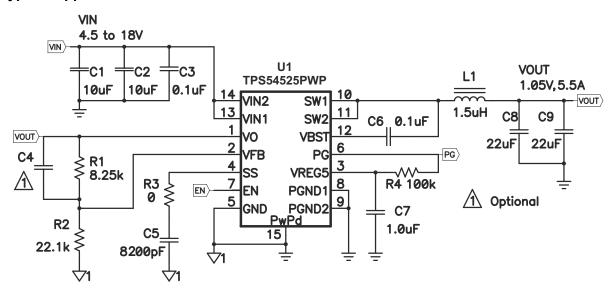


図 8-1. Schematic Diagram

8.2.1 Design Requirements

For this design example, use the following input parameters:

 PARAMETER
 VALUE

 Input voltage range
 4.5 V – 18 V

 Output voltage
 1.05 V

 Output current rating
 0 A – 5.5 A

 Output voltage ripple
 7 mV_{PP} (12 V_{IN} / 5.5 A)

表 8-1. Design Parameters

8.2.2 Detailed Design Procedure

8.2.2.1 Step By Step Design Procedure

To begin the design process, you must know a few application parameters:

- Input voltage range
- Output voltage
- Output current
- Output voltage ripple
- Input voltage ripple

8.2.2.2 Output Voltage Resistors Selection

The output voltage is set with a resistor divider from the output node to the VFB pin. It is recommended to use 1% tolerance or better divider resistors. Start by using \pm 2 to calculate V_{OUT} .

To improve efficiency at very light loads consider using larger value resistors, too high of resistance will be more susceptible to noise and voltage errors from the VFB input current will be more noticeable.

$$V_{\text{OUT}} = \left(0.7651 - 0.0011 \times \text{VOUT_SET}\right) \times \left(1 + \frac{\text{R1}}{\text{R2}}\right)$$
 where VOUT_SET is target VOUT voltage

8.2.2.3 Output Filter Selection

The output filter used with the TPS54525 is an LC circuit. This LC filter has double pole at:

$$F_{P} = \frac{1}{2\pi \sqrt{L_{OUT} \times C_{OUT}}}$$
(3)

At low frequencies, the overall loop gain is set by the output set-point resistor divider network and the internal gain of the TPS54525. The low frequency phase is 180 degrees. At the output filter pole frequency, the gain rolls off at a -40 dB per decade rate and the phase drops rapidly. D-CAP2™ introduces a high frequency zero that reduces the gain roll off to -20 dB per decade and increases the phase to 90 degrees one decade above the zero frequency. The inductor and capacitor selected for the output filter must be selected so that the double pole of 式 3 is located below the high frequency zero but close enough that the phase boost provided be the high frequency zero provides adequate phase margin for a stable circuit. To meet this requirement use the values recommended in 表 8-2

Output Voltage (V)	R1 (kΩ)	R2 (kΩ)	C4 (pF) ⁽¹⁾	L1 (µH)	C8 + C9 (µF)
1	6.81	22.1		1.0 - 1.5	22 - 68
1.05	8.25	22.1		1.0 - 1.5	22 - 68
1.2	12.7	22.1		1.0 - 1.5	22 - 68
1.5	21.5	22.1		1.5	22 - 68
1.8	30.1	22.1	5 - 22	1.5	22 - 68
2.5	49.9	22.1	5 - 22	2.2	22 - 68
3.3	73.2	22.1	5 - 22	2.2	22 - 68
5	124	22.1	5 - 22	3.3	22 - 68

表 8-2. Recommended Component Values

(1) Optional

For higher output voltages at or above 1.8 V, additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1.

Since the DC gain is dependent on the output voltage, the required inductor value will increase as the output voltage increases. For higher output voltages at or above 1.8 V, additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using \pm 4, \pm 5 and \pm 6. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current. Use 650 kHz for f_{SW} .

Use 650 kHz for f_{SW} . Make sure the chosen inductor is rated for the peak current of ± 5 and the RMS current of ± 6 .



$$Ilp - p = \frac{V_{OUT}}{V_{IN(max)}} \bullet \frac{V_{IN(max)} - V_{OUT}}{L_O \bullet f_{SW}}$$

$$\tag{4}$$

$$I_{lpeak} = I_O + \frac{Ilp - p}{2} \tag{5}$$

$$I_{Lo(RMS)} = \sqrt{I_O^2 + \frac{1}{12} I l p - p^2}$$
 (6)

For this design example, the calculated peak current is 6.01 A and the calculated RMS current is 5.5 A. The inductor used is a TDK SPM6530-1R5M100 with a peak current rating of 11.5 A and an RMS current rating of 11 A.

The capacitor value and ESR determines the amount of output voltage ripple. The TPS54525 is intended for use with ceramic or other low ESR capacitors. Recommended values range from 22uF to 68uF. Use 式 7 to determine the required RMS current rating for the output capacitor.

$$I_{CO(RMS)} = \frac{V_{OUT} \bullet (V_{IN} - V_{OUT})}{\sqrt{12} \bullet V_{IN} \bullet L_O \bullet f_{SW}}$$

$$(7)$$

For this design two TDK C3216X5R0J226M 22uF output capacitors are used. The typical ESR is 2 m Ω each. The calculated RMS current is 0.284 A and each output capacitor is rated for 4A.

8.2.2.4 Input Capacitor Selection

The TPS54525 requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A ceramic capacitor over 10 μ F is recommended for the decoupling capacitor. An additional 0.1 μ F capacitor from pin 14 to ground is recommended to improve the EMI performance. The capacitor voltage rating needs to be greater than the maximum input voltage.

8.2.2.5 Bootstrap Capacitor Selection

A 0.1 μF ceramic capacitor must be connected between the VBST to SW pin for proper operation. It is recommended to use a ceramic capacitor.

8.2.2.6 VREG5 Capacitor Selection

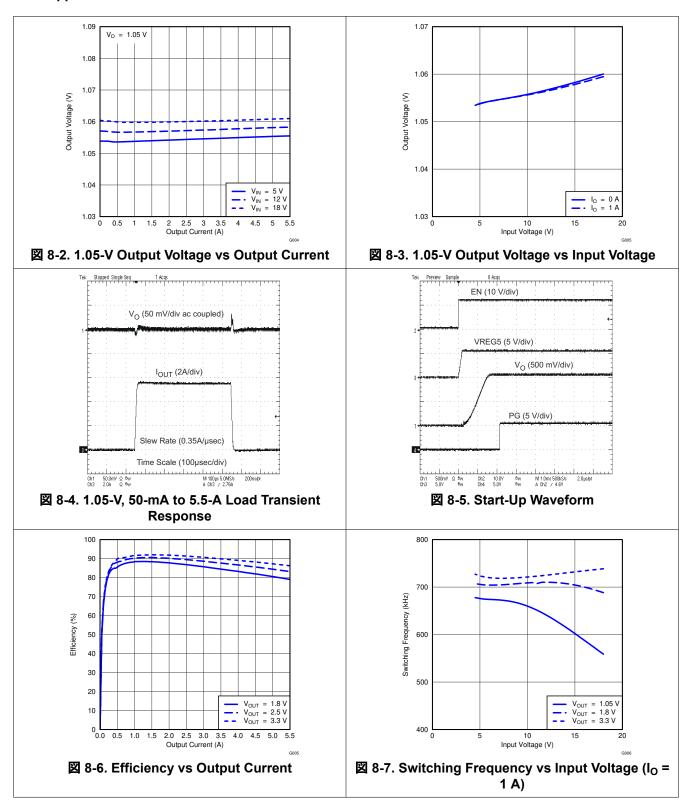
A 1.0 μ F ceramic capacitor must be connected between the VREG5 to GND pin for proper operation. It is recommended to use a ceramic capacitor.

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8.2.3 Application Curves



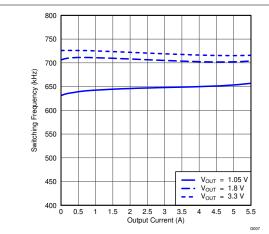




図 8-8. Switching Frequency vs Output Current

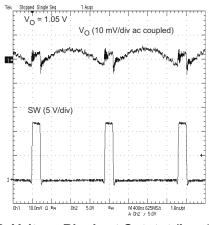
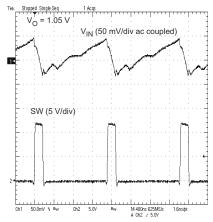


図 8-9. Voltage Ripple at Outptut (I_O = 5.5 A)





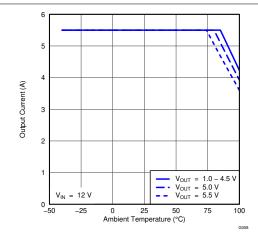


図 8-11. Output Current vs Ambient Temperature



9 Power Supply Recommendations

The device is designed to operate from an input voltage supply range between 4.5 V and 18 V. This input supply should be well regulated. If the input supply is located more than a few inches from the TPS54525 converter additional bulk capacitance may be required in addition to the ceramic bypass capacitors. An electrolytic capacitor with a value of $100~\mu F$ is a typical choice.



10 Layout

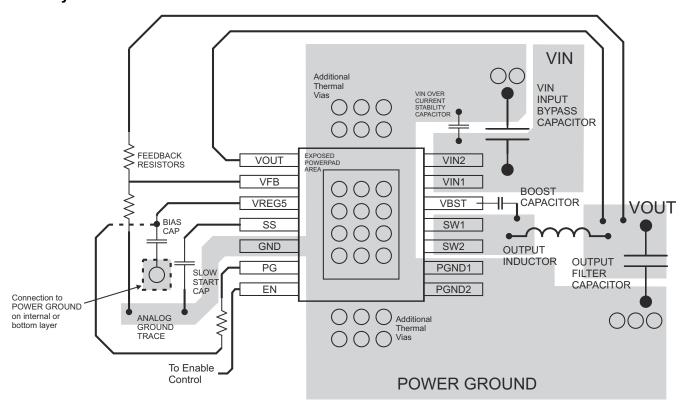
10.1 Layout Guidelines

- · Keep the input switching current loop as small as possible.
- Keep the SW node as physically small and short as possible to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin of the device.
- Keep analog and non-switching components away from switching components.
- Make a single point connection from the signal ground to power ground.
- · Do not allow switching current to flow under the device.
- VREG5 capacitor should be placed near the device, and connected PGND.
- Output capacitor should be connected to a broad pattern of the PGND.
- Voltage feedback loop should be as short as possible, and preferably with ground shield.
- Lower resistor of the voltage divider which is connected to the VFB pin should be tied to SGND.
- Providing sufficient via is preferable for VIN, SW and PGND connection.
- PCB pattern for VIN and SW should be as broad as possible.
- VIN Capacitor should be placed as near as possible to the device.
- The top side power ground (PGND) copper fill area near the IC should be as large as possible. This will aid in thermal dissipation as well lower conduction losses in the ground return
- Exposed pad of device must be connected to PGND with solder. The PGND area under the IC should be as
 large as possible and completely cover the exposed thermal pad. The bottom side of the board should
 contain a large copper area under the device that is directly connected to the exposed area with small
 diameter vias. Small diameter vias will prevent solder from being drawn away from the exposed thermal pad.
 Any additional internal layers should also contain copper ground areas under the device and be connected to
 the thermal vias.

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10.2 Layout Guidelines



VIA to Ground Plane

 --- Etch on Bottom Layer or Under Component

図 10-1. PCB Layout

10.2.1 Thermal Considerations

This PowerPad™ package incorporates an exposed thermal pad that is designed to be directly to an external heartsick. The thermal pad must be soldered directly to the printed board (PCB). After soldering, the PCB can be used as a heartsick. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heartsick structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD™ package and how to use the advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD™ Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD™ Made Easy, Texas Instruments Literature No. SLMA004.

The exposed thermal pad dimensions for this package are shown in the following illustration.



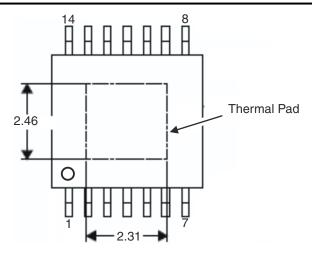


図 10-2. Thermal Pad Dimensions



11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

11.1 Device Support

11.1.1 Third-Party Products Disclaimer

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11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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11.6 用語集

TI 用語集 この用語集には、用語や略語の一覧および定義が記載されています。

www.ti.com 9-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TPS54525PWP	Active	Production	HTSSOP (PWP) 14	90 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525
TPS54525PWP.B	Active	Production	HTSSOP (PWP) 14	90 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525
TPS54525PWPR	Active	Production	HTSSOP (PWP) 14	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525
TPS54525PWPR.B	Active	Production	HTSSOP (PWP) 14	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525
TPS54525PWPRG4	Active	Production	HTSSOP (PWP) 14	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525
TPS54525PWPRG4.B	Active	Production	HTSSOP (PWP) 14	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

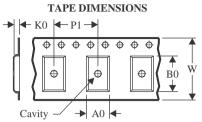
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

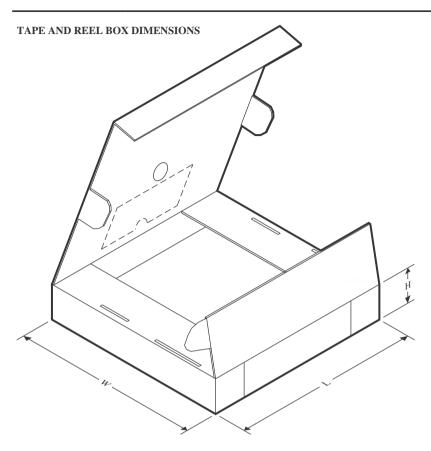
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS54525PWPR	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TPS54525PWPRG4	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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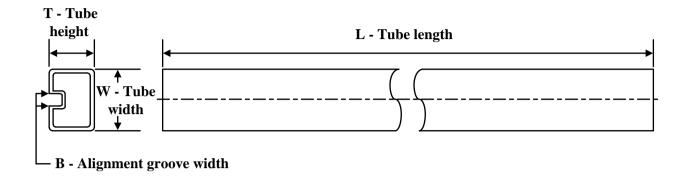
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS54525PWPR	HTSSOP	PWP	14	2000	353.0	353.0	32.0
TPS54525PWPRG4	HTSSOP	PWP	14	2000	353.0	353.0	32.0

PACKAGE MATERIALS INFORMATION

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TUBE



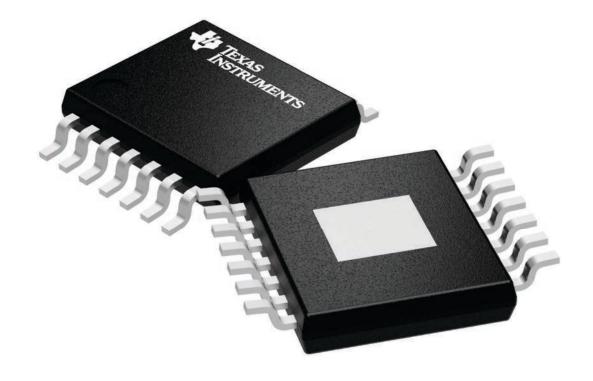
*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPS54525PWP	PWP	HTSSOP	14	90	530	10.2	3600	3.5
TPS54525PWP.B	PWP	HTSSOP	14	90	530	10.2	3600	3.5

4.4 x 5.0, 0.65 mm pitch

PLASTIC SMALL OUTLINE

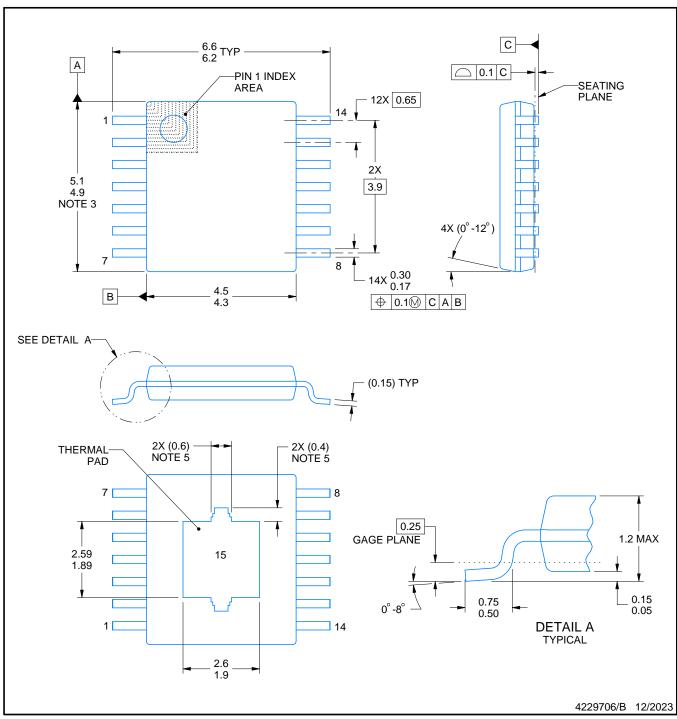
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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PowerPAD[™] TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

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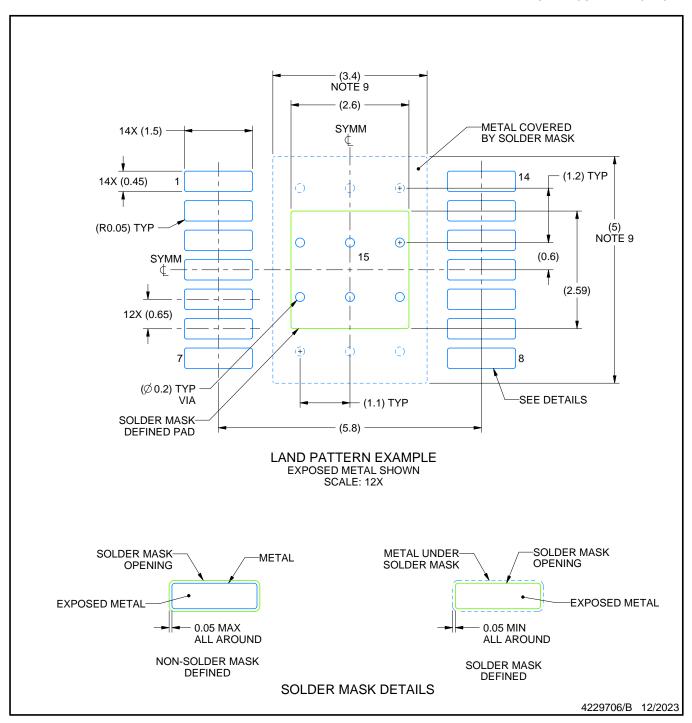
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-153.
- 5. Features may differ or may not be present.



SMALL OUTLINE PACKAGE

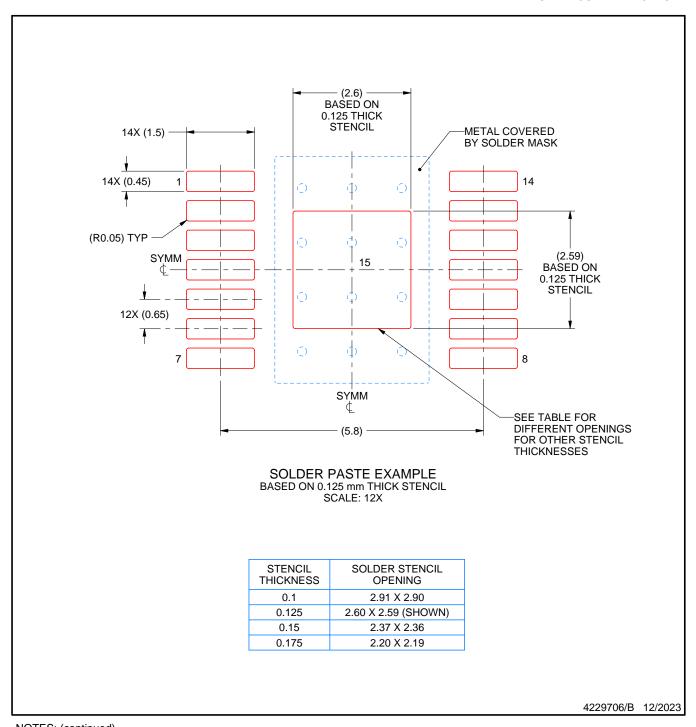


NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.
- 10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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